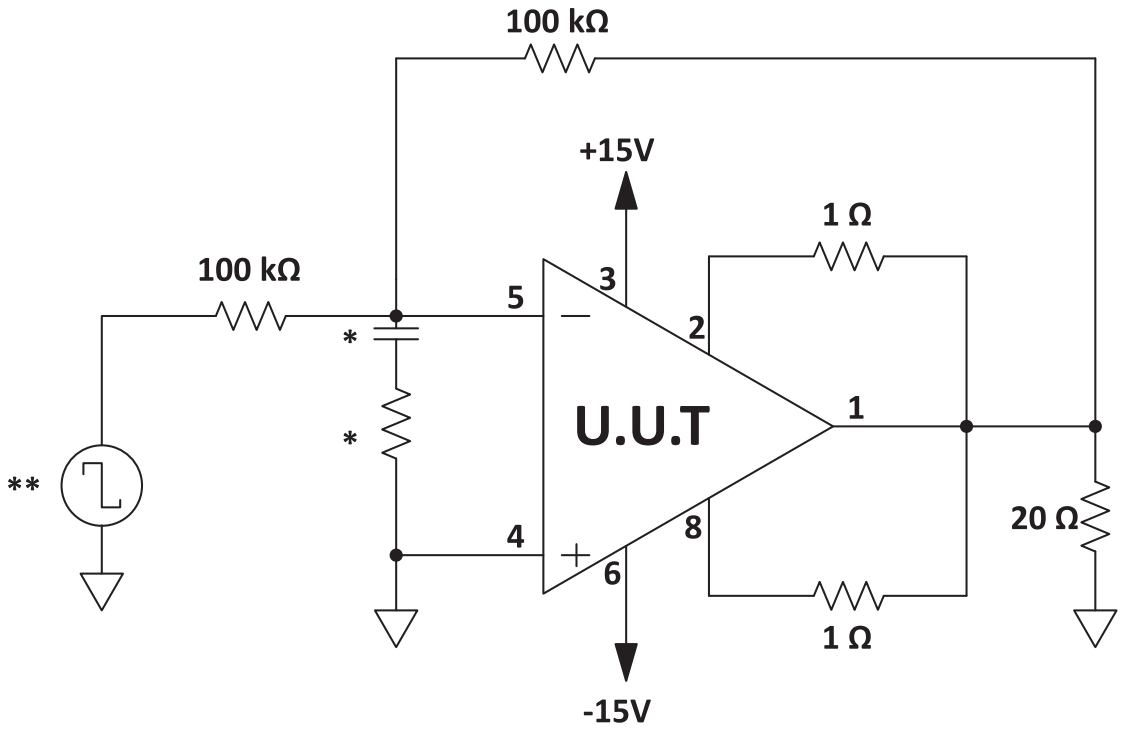
Table 4 Group A Inspection

SG	Parameter	Symbol	Temp.	Power	Test Conditions	Min	Max	Units
1	Quiescent Current	I_Q	25°C	±40V	V_{IN}=0, A_V=100, R_{CL}= 0.1 Ω		30	mA
1	Input Offset Voltage	V_{OS}	25°C	±40V	V_{IN} = 0, A_V = 100		±6	mV
1	Input Offset Voltage	V_{OS}	25°C	±10V	V_{IN} = 0, A_V = 100		±12	mV
1	Input Offset Voltage	V_{OS}	25°C	±45V	V_{IN} = 0, A_V = 100		±7	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±40V	V_{IN} = 0		±30	pA
1	Input Bias Current, –IN	$-I_B$	25°C	±40V	V_{IN} = 0		±30	pA
1	Input Offset Current	I_{OS}	25°C	±40V	V_{IN} = 0		±30	pA
3	Quiescent Current	I_Q	–55°C	±40V	V_{IN}=0, A_V=100, R_{CL}= 0.1 Ω		75	mA
3	Input Offset Voltage	V_{OS}	–55°C	±40V	V_{IN} = 0, A_V = 100		±11.2	mV
3	Input Offset Voltage	V_{OS}	–55°C	±10V	V_{IN} = 0, A_V = 100		±17.2	mV
3	Input Offset Voltage	V_{OS}	–55°C	±45V	V_{IN} = 0, A_V = 100		±12.2	mV
3	Input Bias Current, +IN	$+I_B$	–55°C	±40V	V_{IN} = 0		±115	pA
3	Input Bias Current, –IN	$-I_B$	–55°C	±40V	V_{IN} = 0		±115	pA
3	Input Offset Current	I_{OS}	–55°C	±40V	V_{IN} = 0		±115	pA
2	Quiescent Current	I_Q	125°C	±40V	V_{IN}=0, A_V=100, R_{CL}= 0.1 Ω		30	mA
2	Input Offset Voltage	V_{OS}	125°C	±40V	V_{IN} = 0, A_V = 100		±12.5	mV
2	Input Offset Voltage	V_{OS}	125°C	±10V	V_{IN} = 0, A_V = 100		±18.5	mV
2	Input Offset Voltage	V_{OS}	125°C	±45V	V_{IN} = 0, A_V = 100		±13.5	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±40V	V_{IN} = 0		±70	nA
2	Input Bias Current, –IN	$-I_B$	125°C	±40V	V_{IN} = 0		±70	nA
2	Input Offset Current	I_{OS}	125°C	±40V	V_{IN} = 0		±70	nA
4	Output Voltage, I_O = 5A	V_O	25°C	±18V	R_L = 2.07 Ω	10		V
4	Output Voltage, I_O = 80mA	V_O	25°C	±45V	R_L = 500 Ω	40		V
4	Output Voltage, I_O = 2A	V_O	25°C	±30V	R_L = 12 Ω	24		V
4	Current Limits	I_{CL}	25°C	±17V	R_L = 12 Ω, R_{CL} = 1 Ω	0.6	0.89	A
4	Stability/Noise	E_N	25°C	±40V	R_L = 100 Ω, A_V = 1, C_L = 0.33nF		1	mV
4	Slew Rate	SR	25°C	±40V	R_L = 500 Ω	2	10	V/µs
4	Open Loop Gain	A_{OL}	25°C	±40V	R_L = 500 Ω, F = 10 Hz	96		dB
4	Common Mode Rejection	CMR	25°C	±15V	R_L=500Ω, F=DC, V_{CM}=±9V	74		dB

SG	Parameter	Symbol	Temp.	Power	Test Conditions	Min	Max	Units
6	Output Voltage, I_O = 5A	V_O	–55°C	±18V	R_L = 2.07 Ω	10		V
6	Output Voltage, I_O = 80mA	V_O	–55°C	±45V	R_L = 500 Ω	40		V
6	Output Voltage, I_O = 2A	V_O	–55°C	±30V	R_L = 12 Ω	24		V
6	Stability/Noise	E_N	–55°C	±40V	R_L = 100 Ω, A_V = 1, C_L = 0.33nF		1	mV
6	Slew Rate	SR	–55°C	±40V	R_L = 500 Ω	2	10	V/µs
6	Open Loop Gain	A_{OL}	–55°C	±40V	R_L = 500 Ω, F = 10 Hz	96		dB
6	Common Mode Rejection	CMR	–55°C	±15V	R_L=500Ω, F=DC, V_{CM}=±9V	74		dB
5	Output Voltage, I_O = 3A	V_O	125°C	±14.3V	R_L = 2.07 Ω	6.3		V
5	Output Voltage, I_O = 80mA	V_O	125°C	±45V	R_L = 500 Ω	40		V
5	Output Voltage, I_O = 2A	V_O	125°C	±30V	R_L = 12 Ω	24		V
5	Stability/Noise	E_N	125°C	±40V	R_L = 100 Ω, A_V = 1, C_L = 0.33nF		1	mV
5	Slew Rate	SR	125°C	±40V	R_L = 500 Ω	2	10	V/µs
5	Open Loop Gain	A_{OL}	125°C	±40V	R_L = 500 Ω, F = 10 Hz	96		dB
5	Common Mode Rejection	CMR	125°C	±15V	R_L=500Ω, F=DC, V_{CM}=±9V	74		dB

BURN IN CIRCUIT

Figure 1: Burn In Circuit



*These components are used to stabilize device due to poor high frequency characteristics of burn in board.
**Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.